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CERTIFICATE OF MAILING

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Cameron S. Gilligan

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	)
Takeshi FUKUNAGA et al.	)
Serial No. 08/781,920	) Art Unit: 1112
Filed: December 30, 1996	) Examiner: M. Padgett
For: METHOD OF MANUFACTURING	)
A SEMICONDUCTOR DEVICE	) Date: February 23, 1998

INFORMATION DISCLOSURE STATEMENT
AND CROSS-REFERENCE OF RELATED APPLICATIONS

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

Pursuant to Applicant's duty of candor under 37 C.F.R. §1.56, Applicant wishes to inform the Examiner of the following applications claiming related technical subject matter:

Serial No.	Filing Date	Title
08/520,079	Aug. 28, 1995	Semiconductor Circuit for Electro-Optical Device and Method of Manufacturing the Same
08/769,113	Dec. 18, 1996	Semiconductor Circuit for Electro-Optical Device and Method of Manufacturing the Same
08/865,047	May 29, 1997	Thin Film Type Monolithic Semiconductor Device

U.S. Patent Nos. 5,403,772; 5,639,968; 5,604,360; 5,481,121; 5,488,000; 5,529,937; 5,663,077; 5,492,843; 5,508,533; 5,534,716; 5,643,826; 5,543,352; 5,563,426; 5,585,291; 5,616,506; 5,608,232; 5,612,250; 5,654,203; 5,614,426; 5,621,224; and 5,637,515 teach the crystal growth in the lateral direction.

Adding a solution comprising the catalyst material therein is disclosed in the U.S. Patent Nos. 5,639,698; 5,643,826; 5,543,352; 5,585,291; 5,605,846; 5,608,232; 5,612,250; 5,654,203; and 5,621,224.

U.S. Patent No. 5,639,698 discloses annealing a semiconductor film in a halogen atmosphere after crystallization by heating in order to remove a catalytic material in the semiconductor film.

U.S. Patent No. 5,595,923 indicates annealing at a temperature after crystallization in order to promote further crystallization and to activate

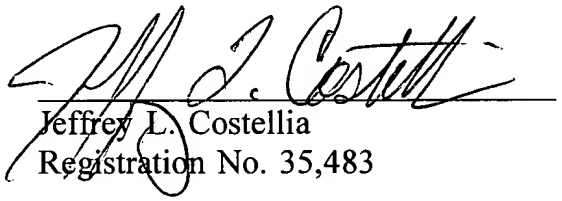
introduced impurities.

U.S. Patent No. 5,700,333 teaches heating the crystallized semiconductor film to activate phosphorus in the semiconductor film so that a catalytic metal for crystallization of the semiconductor film therein can be gettered.

Submitted herewith is the requisite fee of $240.00. Hence, it is requested that the references submitted herewith be considered and made of record in the subject application.

Copies of the references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

Respectfully submitted,



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